



## DMN33D8LDWQ

## **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>A</sub> = +25°C
	$3\Omega @ V_{GS} = 4.5V$	250mA
30V	5Ω @ V <sub>GS</sub> = 4.0V	200mA
	7Ω @ V <sub>GS</sub> = 2.5V	100mA

## **Description and Applications**

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Motor Control
- DC-DC Converters
- Backlighting

# ESD PROTECTED



SOT363

Top View

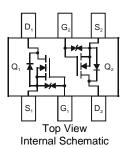
## **DUAL N-CHANNEL ENHANCEMENT MODE MOSFET**

### Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- ESD Protected
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

## **Mechanical Data**

- Case: SOT363
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Alloy 42 Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.006 grams (Approximate)



## Ordering Information (Note 5)

	Part Number	Case	Packaging					
	DMN33D8LDWQ-7	SOT363	3,000/Tape & Reel					
	DMN33D8LDWQ-13	SOT363	10,000/Tape & Reel					
Notes:	Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS). 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.							

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and

2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to https://www.diodes.com/quality/.

5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

## **Marking Information**

					$\square$
	I	<b>V</b> 33	;	ΥM	
		٨X	8	A33	I
Г					

N33 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: G = 2019) M = Month (ex: 9 = September)

Date	Code	Kev
Daie	COUE	1109

	004	•	2020		2024		22	0000		0004		005
Year	201	9	2020		2021	20	22	2023		2024	4	2025
Code	G		Н		I		J	K		L		Μ
Month	Jan	Feb	Mar	Apr	Mav	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Month	Uan	100	Inici		may	Juli	oui	Aug	Ocp	001	1101	Dee
Code												



# Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		V <sub>DSS</sub>	30	V
Gate-Source Voltage	V <sub>GSS</sub>	±20	V	
Continuous Drain Current (Note 6) $V_{GS} = 4.5V$ State State T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C		ID	250 200	mA
Maximum Continuous Body Diode Forward Curren	t (Note 6)	Is	0.5	А
Pulsed Drain Current (10µs Pulse, Duty Cycle=1%)	)	I <sub>DM</sub>	0.8	A

## Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 6)	T <sub>A</sub> = +25°C	P	0.35	w
Total Power Dissipation (Note 6)	$T_A = +70^{\circ}C$	PD	0.22	vv
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R <sub>0JA</sub>	360	0CM/
Thermal Resistance, Junction to Case	R <sub>θJC</sub>	126	°C/W	
Operating and Storage Temperature Range		T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	°C

# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

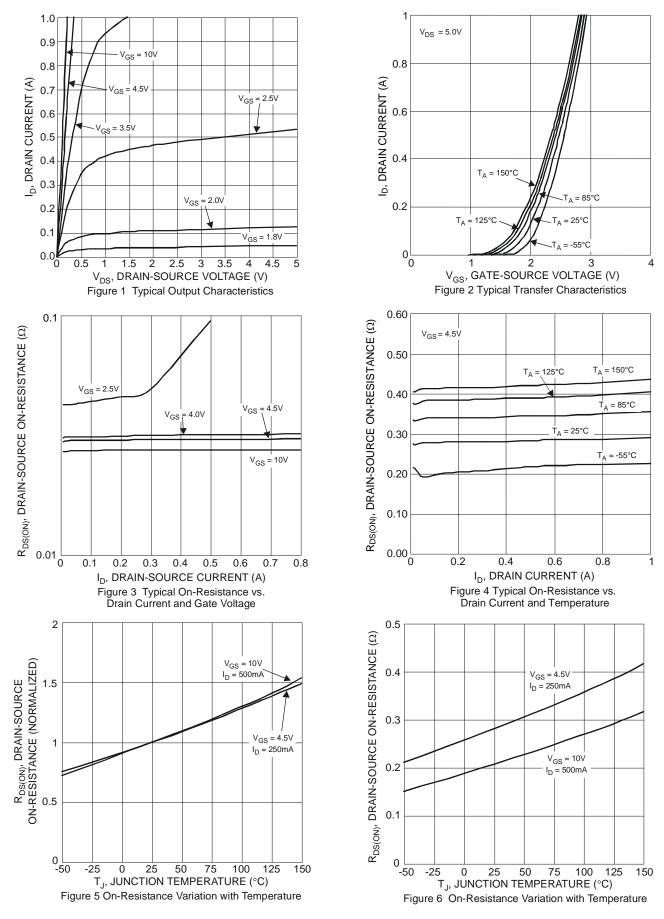
			-		-	-	
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)				-		. <u>.</u>	
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	30	_		V	$V_{GS} = 0V, I_D = 1mA$	
Zero Gate Voltage Drain Current $@T_C = +25^{\circ}C$	IDSS		_	1	μA	$V_{DS} = 30V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>			±10	μA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	0.8		1.5	V	$V_{DS} = 3V, I_{D} = 100 \mu A$	
			_	2.4		$V_{GS} = 10V, I_D = 250mA$	
Static Drain-Source On-Resistance		_	_	3.0	Ω	$V_{GS} = 4.5V, I_D = 250mA$	
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	_	_	5.0	Ω	$V_{GS} = 4.0V, I_{D} = 10mA$	
		_	_	7.0		$V_{GS} = 2.5V, I_D = 5mA$	
Diode Forward Voltage	V <sub>SD</sub>	_	_	1.2	V	$V_{GS} = 0V, I_{S} = 115mA$	
DYNAMIC CHARACTERISTICS (Note 8)						·	
Input Capacitance	Ciss	_	48	—	pF		
Output Capacitance	Coss	_	11	_	pF	V <sub>DS</sub> = 5V, V <sub>GS</sub> = 0V, f = 1.0MHz	
Reverse Transfer Capacitance	Crss	_	8	_	pF		
Gate Resistance	Rg	_	57	—	Ω	f=1MHz, V <sub>GS</sub> =0V, V <sub>DS</sub> =0V	
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Qg	_	0.55	—	nC		
Total Gate Charge (V <sub>GS</sub> = 10V)		_	1.23	_	nC	)/ 10)/ L 050m A	
Gate-Source Charge	Q <sub>gs</sub>	_	0.14	_	nC	$V_{DS} = 10V, I_D = 250mA$	
Gate-Drain Charge	Q <sub>gd</sub>	_	0.14	—	nC	1	
Turn-On Delay Time	t <sub>D(ON)</sub>		2.9	—	ns		
Turn-On Rise Time	t <sub>R</sub>		2.6	_	ns	$V_{DD} = 30V, V_{GS} = 10V,$	
Turn-Off Delay Time	t <sub>D(OFF)</sub>		18.2	—	ns	$R_{G} = 25\Omega, I_{D} = 200 \text{mA}$	
Turn-Off Fall Time	t <sub>F</sub>		13.6	—	ns	1	

Notes: 6. Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.

Short duration pulse test used to minimize self-heating effect.
Guaranteed by design. Not subject to product testing.

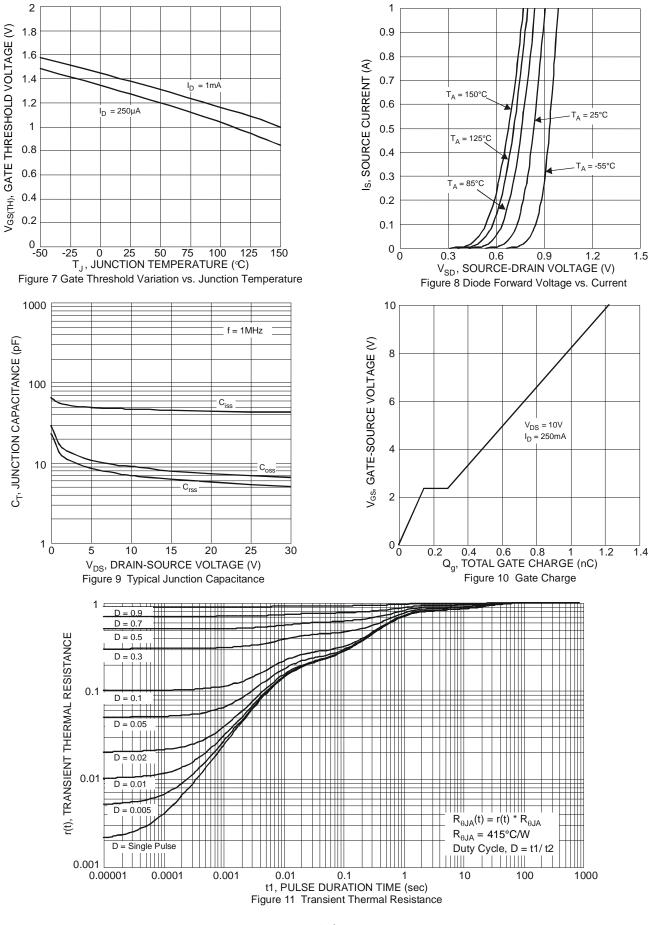


# DMN33D8LDWQ





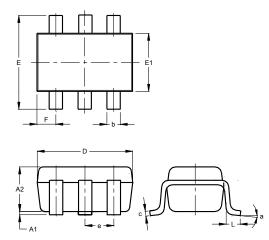
## DMN33D8LDWQ





# **Package Outline Dimensions**

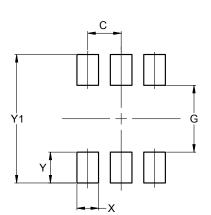
Please see http://www.diodes.com/package-outlines.html for the latest version.



SOT363										
Dim	Min Max Typ									
A1	0.00	0.10	0.05							
A2	0.90 1.00 0.95									
b	0.10	0.30	0.25							
c	0.10	0.22	0.11							
D	1.80	2.20	2.15							
Е	2.00	2.20	2.10							
E1	1.15	1.30								
е	C	).650 E	SC							
F	0.40	0.45	0.425							
_	0.25	0.40	0.30							
а	0°	8°								
All I	Dimen	sions	in mm							

## **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.



SOT363

Dimensions	Value (in mm)
С	0.650
•	
G	1.300
Х	0.420
Y	0.600
Y1	2.500

SOT363



#### **IMPORTANT NOTICE**

DIODES INCORPORATED MAKES NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. Diodes Incorporated does not assume any liability arising out of the application or use of this document or any product described herein; neither does Diodes Incorporated convey any license under its patent or trademark rights, nor the rights of others. Any Customer or user of this document or products described herein in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on Diodes Incorporated website, harmless against all damages.

Diodes Incorporated does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel. Should Customers purchase or use Diodes Incorporated products for any unintended or unauthorized application, Customers shall indemnify and hold Diodes Incorporated and its representatives harmless against all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized application.

Products described herein may be covered by one or more United States, international or foreign patents pending. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks.

This document is written in English but may be translated into multiple languages for reference. Only the English version of this document is the final and determinative format released by Diodes Incorporated.

#### LIFE SUPPORT

Diodes Incorporated products are specifically not authorized for use as critical components in life support devices or systems without the express written approval of the Chief Executive Officer of Diodes Incorporated. As used herein:

- A. Life support devices or systems are devices or systems which:
  - 1. are intended to implant into the body, or
  - 2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.
- B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

Customers represent that they have all necessary expertise in the safety and regulatory ramifications of their life support devices or systems, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of Diodes Incorporated products in such safety-critical, life support devices or systems, notwithstanding any devices- or systems-related information or support that may be provided by Diodes Incorporated. Further, Customers must fully indemnify Diodes Incorporated and its representatives against any damages arising out of the use of Diodes Incorporated products in such safety-critical, life support devices or systems.

Copyright © 2019, Diodes Incorporated

www.diodes.com

单击下面可查看定价,库存,交付和生命周期等信息

>>Diodes Incorporated(达迩科技(美台))